



BUK9875-100A

N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

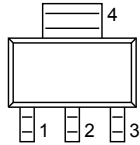
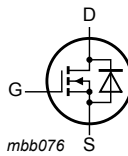
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 5\text{ V}$; $T_{sp} = 25\text{ °C}$; Fig. 2 ; Fig. 3	-	-	7	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$; Fig. 1	-	-	8	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 8\text{ A}$; $T_j = 25\text{ °C}$	-	-	84	m Ω
		$V_{GS} = 10\text{ V}$; $I_D = 8\text{ A}$; $T_j = 25\text{ °C}$	-	62	72	m Ω
		$V_{GS} = 5\text{ V}$; $I_D = 8\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12 ; Fig. 13	-	64	75	m Ω
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 7\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	-	49	mJ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SC-73 (SOT223)</p>	 <p><i>mbb076</i></p>
2	D	drain		
3	S	source		
4	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9875-100A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BUK9875-100A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9875-100A	987510A
BUK9875-100A/CU	987510

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$; $T_j \leq 150\text{ }^\circ\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-10	10	V
P_{tot}	total power dissipation	$T_{sp} = 25\text{ }^\circ\text{C}$; Fig. 1	-	8	W
I_D	drain current	$T_{sp} = 25\text{ }^\circ\text{C}$; $V_{GS} = 5\text{ V}$; Fig. 2 ; Fig. 3	-	7	A
		$T_{sp} = 100\text{ }^\circ\text{C}$; $V_{GS} = 5\text{ V}$; Fig. 2	-	4	A
I_{DM}	peak drain current	$T_{sp} = 25\text{ }^\circ\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3	-	28	A

Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-55	150	°C
T _j	junction temperature		-55	150	°C
V _{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 μs	-15	15	V
Source-drain diode					
I _S	source current	T _{sp} = 25 °C	-	7	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{sp} = 25 °C	-	28	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 7 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{j(init)} = 25 °C; unclamped	-	49	mJ

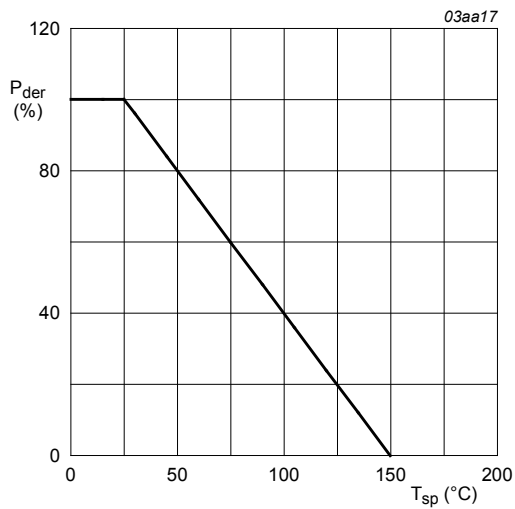


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

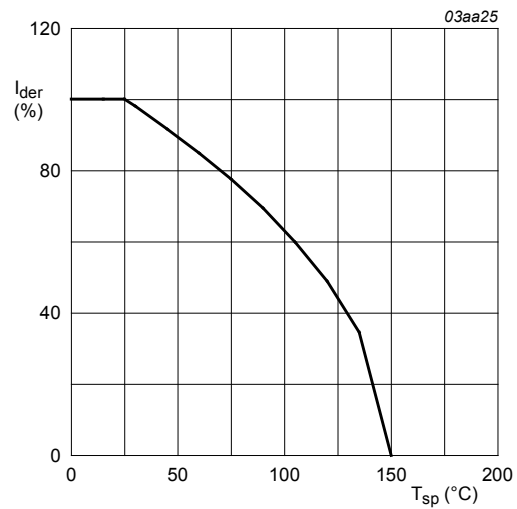


Fig. 2. Normalized continuous drain current as a function of solder point temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

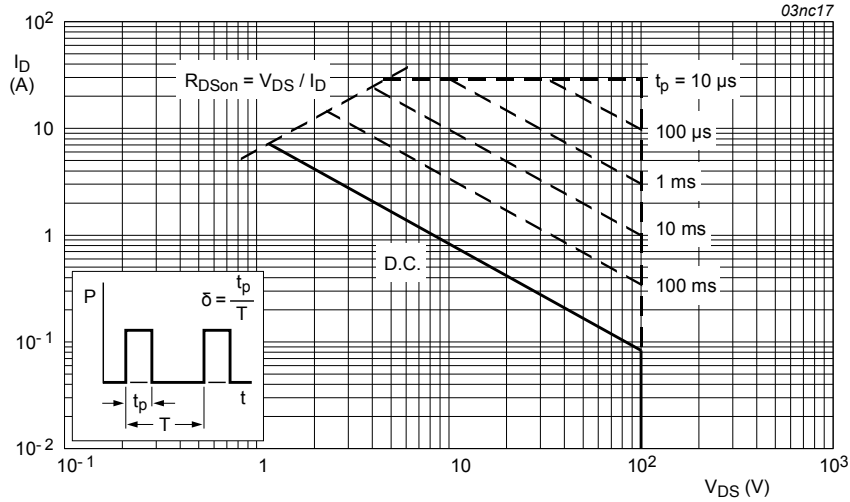


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{amb} = 25^\circ C; I_{DM}$ is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 4	-	120	-	K/W

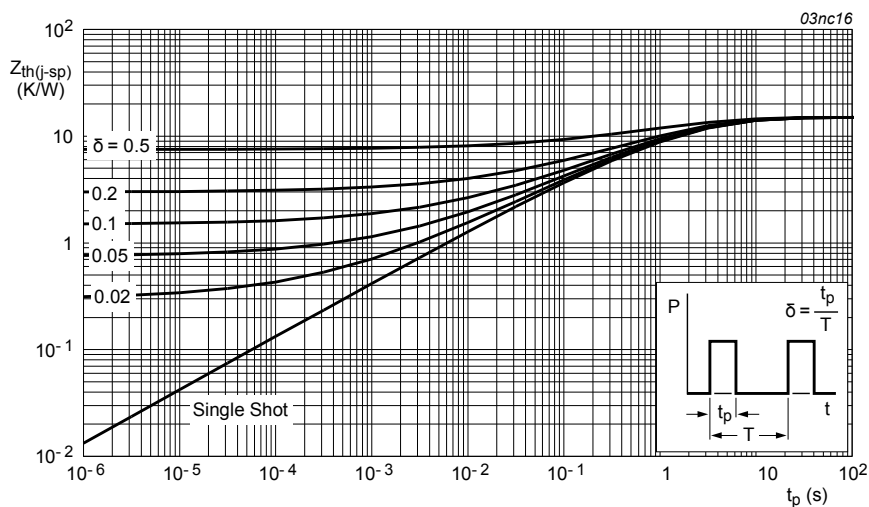


Fig. 4. Transient thermal impedance from junction to solder point as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	100	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 11	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ Fig. 11	-	-	2.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ\text{C};$ Fig. 11	0.6	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ }^\circ\text{C}$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 8 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ Fig. 12; Fig. 13	-	-	162	m Ω
		$V_{GS} = 4.5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	-	84	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	62	72	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 12; Fig. 13	-	64	75	m Ω
Dynamic characteristics						
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ Fig. 14	-	1270	1690	pF
C_{oss}	output capacitance		-	140	167	pF
C_{rss}	reverse transfer capacitance		-	90	124	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 10 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	13	-	ns
t_r	rise time		-	120	-	ns
$t_{d(off)}$	turn-off delay time		-	58	-	ns
t_f	fall time		-	57	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ Fig. 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$	-	63	-	ns
Q_r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	220	-	nC

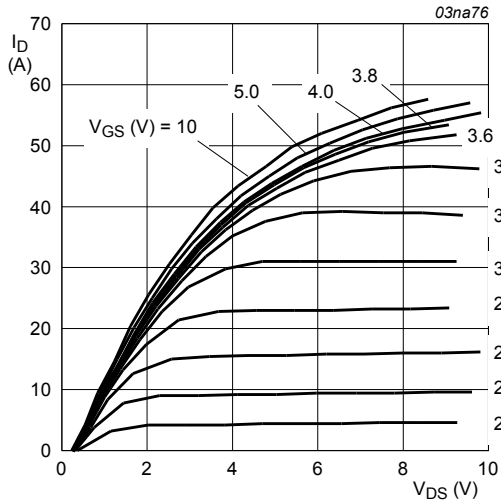


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

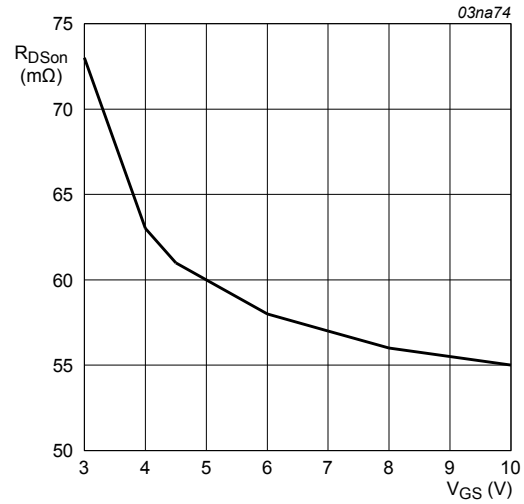


Fig. 6. Drain-source on-state resistance as a function of gate-source; typical values

$T_j = 25^\circ\text{C}; I_D = 8\text{A}$

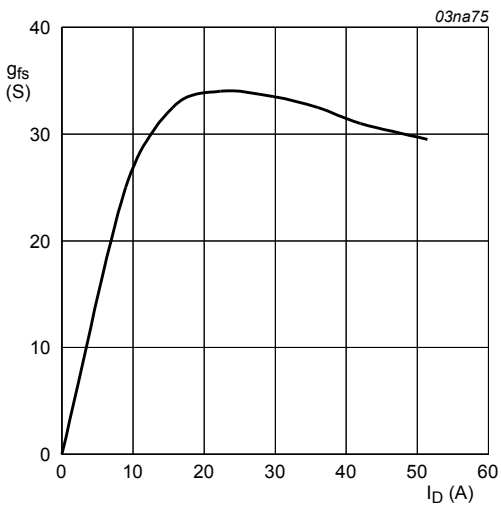
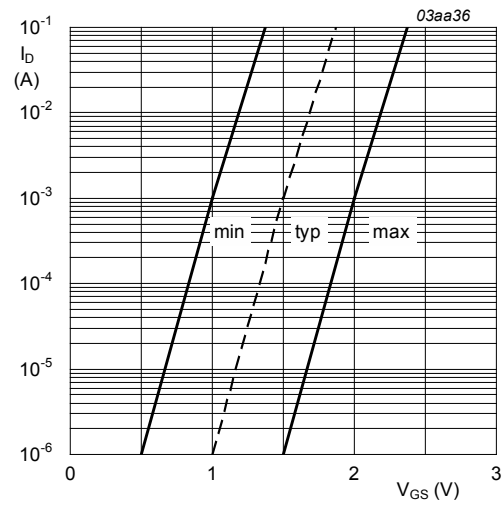


Fig. 7. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$



$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig. 8. Sub-threshold drain current as a function of gate-source voltage

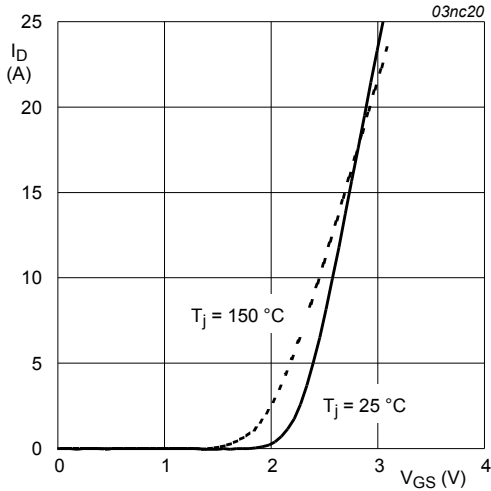


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 25V$

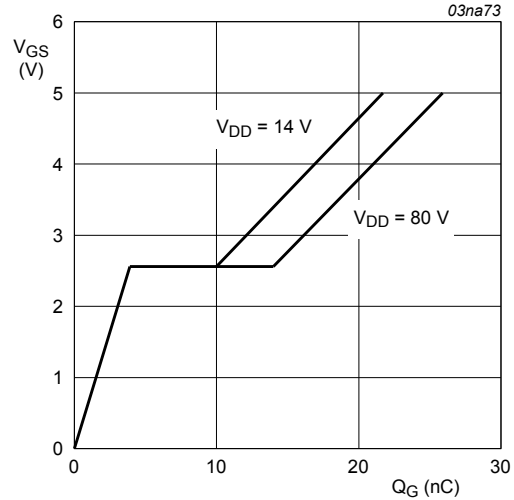


Fig. 10. Gate-source voltage as a function of turn-on gate charge; typical values

$T_j = 25^{\circ}C; I_D = 20A$

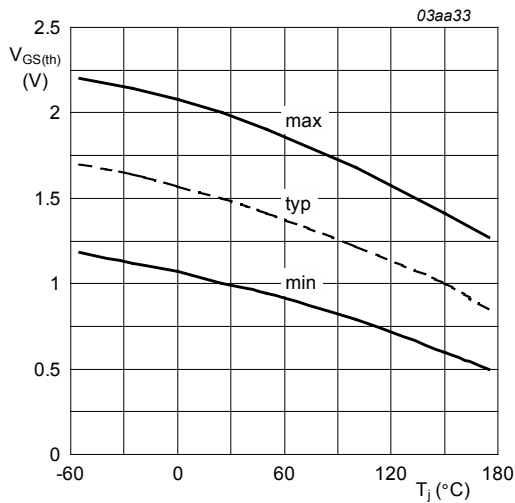


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1mA; V_{DS} = V_{GS}$

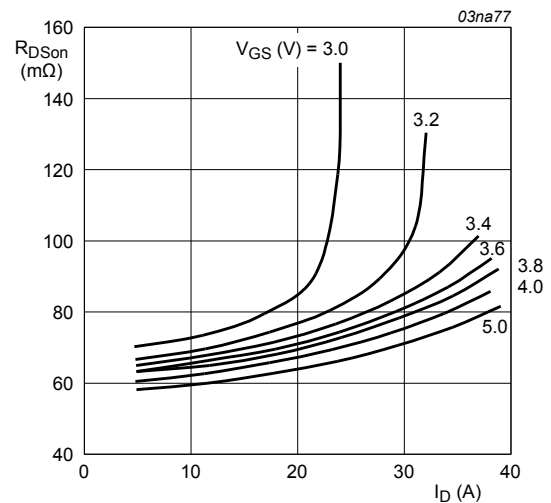


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^{\circ}C$

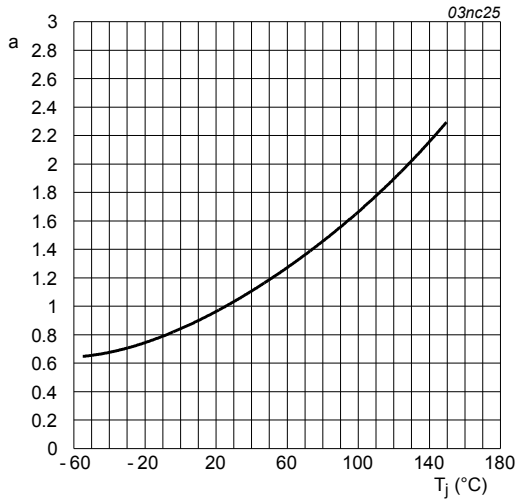


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon@25^\circ C}}$$

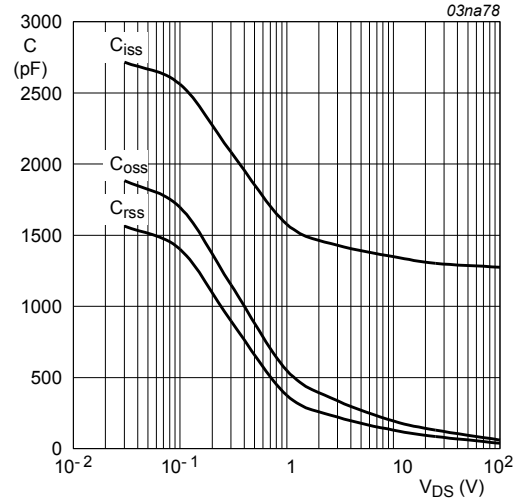


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

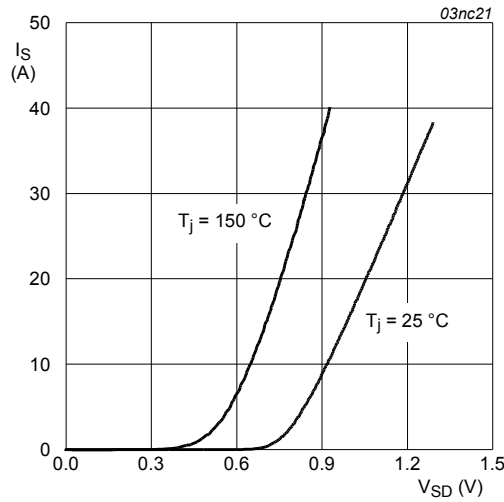


Fig. 15. Reverse diode current as a function of reverse diode voltage; typical value

$$V_{GS} = 0V$$

11. Package outline

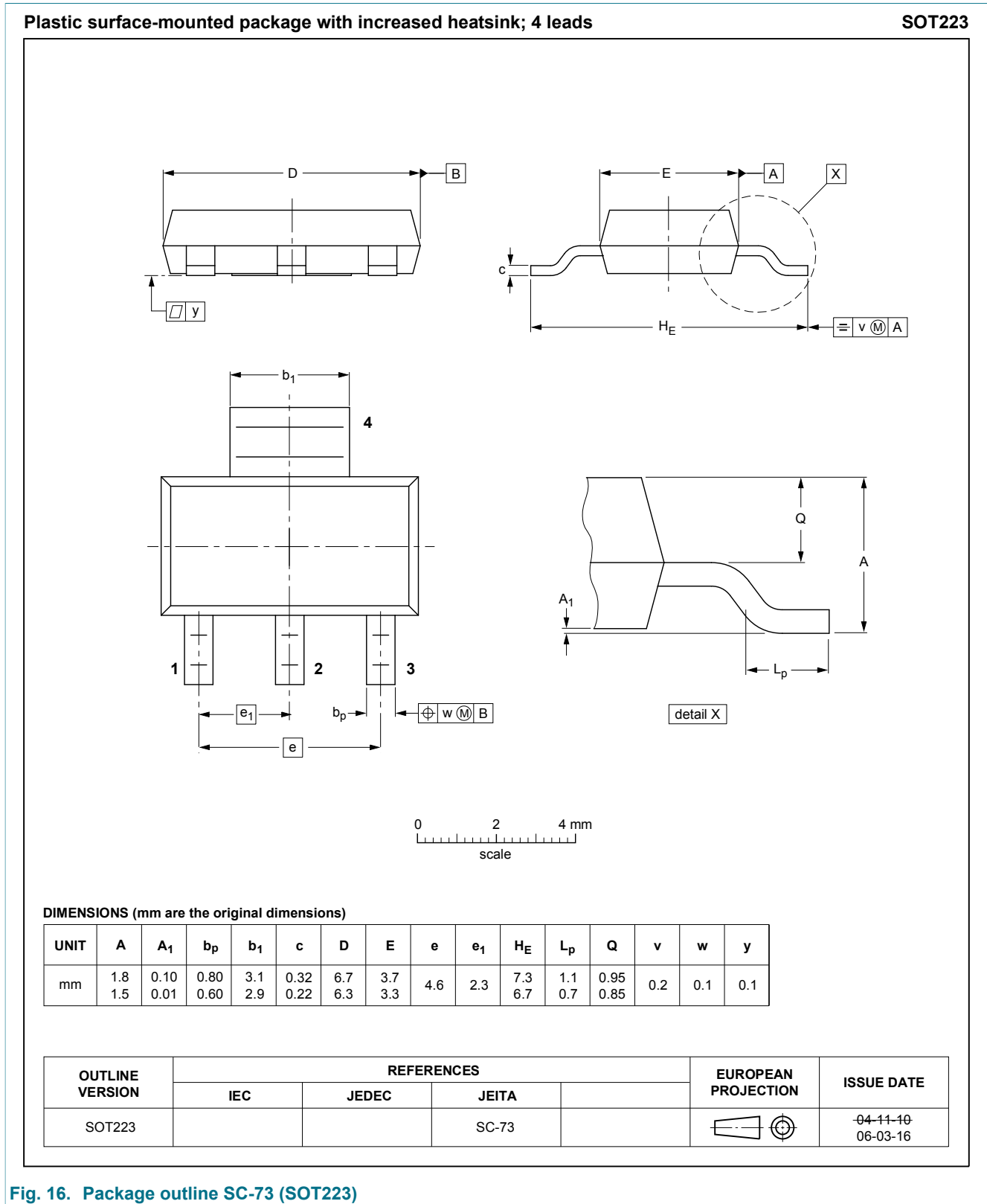


Fig. 16. Package outline SC-73 (SOT223)

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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